

Jordan D Greenlee

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

33
papers

665
citations

16
h-index

25
g-index

34
ext. papers

740
ext. citations

2.4
avg, IF

3.49
L-index

#	Paper	IF	Citations
33	Selective p-type Doping of GaN:Si by Mg Ion Implantation and Multicycle Rapid Thermal Annealing. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P124-P127	2	32
32	Structural, Optical, and Electrical Characterization of Monoclinic β -Ga ₂ O ₃ Grown by MOVPE on Sapphire Substrates. <i>Journal of Electronic Materials</i> , 2016 , 45, 2031-2037	1.9	92
31	Defect reduction in MBE-grown AlN by multicycle rapid thermal annealing. <i>Electronic Materials Letters</i> , 2016 , 12, 133-138	2.9	11
30	Spatial Mapping of Pristine and Irradiated AlGa _N /Ga _N HEMTs With UV Single-Photon Absorption Single-Event Transient Technique. <i>IEEE Transactions on Nuclear Science</i> , 2016 , 63, 1995-2001	1.7	14
29	Hyperspectral Electroluminescence Characterization of OFF-State Device Characteristics in Proton Irradiated High Voltage AlGa _N /Ga _N HEMTs. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, Q289-Q293	2	10
28	Improvements in the Annealing of Mg Ion Implanted GaN and Related Devices. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 2016 , 29, 343-348	2.6	23
27	Improved Vertical GaN Schottky Diodes with Ion Implanted Junction Termination Extension. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, Q176-Q178	2	26
26	Impact of Surface Passivation on the Dynamic ON-Resistance of Proton-Irradiated AlGa _N /Ga _N HEMTs. <i>IEEE Electron Device Letters</i> , 2016 , 37, 545-548	4.4	23
25	Ultraviolet detector based on graphene/SiC heterojunction. <i>Applied Physics Express</i> , 2015 , 8, 041301	2.4	21
24	Elimination of Basal Plane Dislocations in Epitaxial 4H-SiC via Multicycle Rapid Thermal Annealing. <i>Materials Science Forum</i> , 2015 , 821-823, 297-302	0.4	1
23	Symmetric Multicycle Rapid Thermal Annealing: Enhanced Activation of Implanted Dopants in GaN. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, P382-P386	2	32
22	Comparison of AlN Encapsulants for Bulk GaN Multicycle Rapid Thermal Annealing. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, P403-P407	2	10
21	UV Single-Photon Absorption Single-Event Transient Testing of Pristine and Irradiated AlGa _N /Ga _N HEMTs 2015 ,		1
20	Degradation mechanisms of 2 MeV proton irradiated AlGa _N /Ga _N HEMTs. <i>Applied Physics Letters</i> , 2015 , 107, 083504	3.4	26
19	Characterization of an Mg-implanted GaN p ⁺ i ⁻ n diode. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 2772-2775	1.6	28
18	Thermal etching of nanocrystalline diamond films. <i>Diamond and Related Materials</i> , 2015 , 59, 116-121	3.5	8
17	Molecular beam epitaxy growth of niobium oxides by solid/liquid state oxygen source and lithium assisted metal-halide chemistry. <i>Journal of Crystal Growth</i> , 2015 , 425, 225-229	1.6	6

16	Temporary Bonding with Polydimethylglutarimide Based Lift Off Resist as a Layer Transfer Platform. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, P190-P194	2	6
15	Characterization of a selective AlN wet etchant. <i>Applied Physics Express</i> , 2015 , 8, 036501	2.4	15
14	Multicycle rapid thermal annealing optimization of Mg-implanted GaN: Evolution of surface, optical, and structural properties. <i>Journal of Applied Physics</i> , 2014 , 116, 063502	2.5	28
13	Liquid Phase Electro-Epitaxy of Memristive LiNbO ₂ Crystals. <i>Crystal Growth and Design</i> , 2014 , 14, 2218-2232	3.2	11
12	Substrate-Dependent Effects on the Response of AlGaIn/GaN HEMTs to 2-MeV Proton Irradiation. <i>IEEE Electron Device Letters</i> , 2014 , 35, 826-828	4.4	65
11	Proton Radiation-Induced Void Formation in Ni/Au-Gated AlGaIn/GaN HEMTs. <i>IEEE Electron Device Letters</i> , 2014 , 35, 1194-1196	4.4	23
10	Comparison of AlN encapsulants for high-temperature GaN annealing. <i>Applied Physics Express</i> , 2014 , 7, 121003	2.4	10
9	Degradation mechanisms of AlGaIn/GaN HEMTs on sapphire, Si, and SiC substrates under proton irradiation 2014 ,		6
8	Radiation Effects on LiNbO ₃ Memristors for Neuromorphic Computing Applications. <i>IEEE Transactions on Nuclear Science</i> , 2013 , 60, 4555-4562	1.7	12
7	Spatiotemporal drift-diffusion simulations of analog ionic memristors. <i>Journal of Applied Physics</i> , 2013 , 114, 034504	2.5	7
6	Comparison of Interfacial and Bulk Ionic Motion in Analog Memristors. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 427-432	2.9	21
5	In situ Auger probe enabling epitaxy composition control of alloys by elemental surface analysis. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 03C126	1.3	2
4	In situ investigation of the channel conductance of a Li _{1-x} CoO ₂ (0 < x < 1). <i>Applied Physics Letters</i> , 2013 , 102, 213502	3.4	16
3	Halide based MBE of crystalline metals and oxides. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 155-160		18
2	In-situ oxygen x-ray absorption spectroscopy investigation of the resistance modulation mechanism in LiNbO ₂ memristors. <i>Applied Physics Letters</i> , 2012 , 100, 182106	3.4	27
1	Observation and control of the surface kinetics of InGaIn for the elimination of phase separation. <i>Journal of Applied Physics</i> , 2012 , 112, 014909	2.5	34